

## Title (en)

Fabrication of a thin film transistor and production of a liquid crystal display apparatus.

## Title (de)

Herstellung eines Dünnschicht-Transistors und Produktion einer Flüssigkristallanzeige-Vorrichtung.

## Title (fr)

Fabrication d'un transistor à couche mince et production d'un dispositif d'affichage à cristaux liquides.

## Publication

**EP 0592227 A3 19950111 (EN)**

## Application

**EP 93307998 A 19931007**

## Priority

JP 26898192 A 19921007

## Abstract (en)

[origin: EP0592227A2] A thin film transistor includes: an insulating film having a surface; a semiconductor film formed on the surface of the insulating film; a source electrode and a drain electrode which are in contact with the semiconductor film; and a gate electrode which is electrically insulated from the semiconductor film. In the thin film transistor, a portion of the semiconductor film at distances of less than 500 angstroms from the surface of the insulating film contains at least silicon including a microcrystalline structure having a conductivity of  $5 \times 10^{-9}$  S/cm or more. Also, a method for fabricating such a thin film transistor is disclosed. The method includes a step of forming a semiconductor film including a silicon layer having a microcrystalline structure by repeatedly performing the following steps (1) and (2): (1) forming a silicon layer on an insulating film by decomposing a material gas including Si which is introduced into a reaction chamber of a plasma chemical vapor deposition apparatus; and (2) microcrystallizing the silicon layer by introducing the hydrogen gas into the chamber to perform a hydrogen plasma treatment for the silicon layer.

<IMAGE>

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## IPC 8 full level

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## CPC (source: EP KR US)

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## Citation (search report)

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